

	Type	Hits	S arch Text	DBs
1	BRS	2282079	wafer or substrate or die or chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	190239	(second or another or addition\$4) near4 (wafer or substrate or die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	90883	(separat\$4 or cleav\$4) near4 (wafer or substrate or die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	9939	(bond\$4 or join\$4) near4 ((second or another or addition\$4) near4 (wafer or substrate or die or chip))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	2724	((bond\$4 or join\$4) near4 ((second or another or addition\$4) near4 (wafer or substrate or die or chip))) and ((separat\$4 or cleav\$4) near4 (wafer or substrate or die or chip))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	599	((bond\$4 or join\$4) near4 ((second or another or addition\$4) near4 (wafer or substrate or die or chip))) same ((separat\$4 or cleav\$4) near4 (wafer or substrate or die or chip))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	321	(semiconductor or silicon) and (@ay < "1999") and (((bond\$4 or join\$4) near4 ((second or another or addition\$4) near4 (wafer or substrate or die or chip))) same ((separat\$4 or cleav\$4) near4 (wafer or substrate or die or chip)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	90997	(separat\$4 or cleav\$4) near4 (wafer or substrate or die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	S arch T xt	DBs
9	BRS	91022	(separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 (wafer or substrate or die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	414726	mask\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	4465	((separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 (wafer or substrate or die or chip)) same mask\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	1549	((separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 (wafer or substrate or die or chip)) near8 mask\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	14032	(separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 (porous\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	635	(separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 (porous\$4) near4 (wafer or substrate or chip or die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	824	mask\$4 near4 porous\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	10	((separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 (porous\$4) near4 (wafer or substrate or chip or die)) and (mask\$4 near4 porous\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	43	((separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 (porous\$4)) and (mask\$4 near4 porous\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Typ	Hits	Search T xt	DBs
18	BRS	33	((separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 (porous\$4)) and (mask\$4 near4 porous\$4)) not (((separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 (porous\$4) near4 (wafer or substrate or chip or die)) and (mask\$4 near4 porous\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	IS&R	847	((438/960) or (438/455) or (438/455) or (438/459)).CCLS.	USPAT; US-PGPUB
20	BRS	581	((438/960) or (438/455) or (438/455) or (438/459)).CCLS.) and (@ay < "1999")	USPAT
21	BRS	185	((separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 porous\$4) and mask\$4 and (semiconductor or silicion or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	103	((separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 porous\$4) and mask\$4 and (wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	16	((separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 porous\$4) and mask\$4 and (wafer or substrate)) not (((separat\$4 or cleav\$4 or smart-cut\$4 or smart adj cut\$4) near4 porous\$4) and mask\$4 and (semiconductor or silicion or si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	41	((separat\$4 or cleav\$4) near4 porous\$4) and (semiconductor or silicion or si) and (smart-cut\$4 or smart adj cut\$4 or ("h.sub.2" or hydrogen) near4 (inplant\$4 or implant\$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	55	((separat\$4 or cleav\$4) same porous\$4) and (semiconductor or silicion or si) and (smart-cut\$4 or smart adj cut\$4 or ("h.sub.2" or hydrogen) near4 (inplant\$4 or implant\$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	S arch Text	DBs
26	BRS	14	(((((separat\$4 or cleav\$4) same porous\$4) and (semiconductor or silicion or si) and (smart-cut\$4 or smart adj cut\$4 or ("h.sub.2" or hydrogen) near4 (inplant\$4 or implant\$4))))) not (((separat\$4 or cleav\$4) near4 porous\$4) and (semiconductor or silicion or si) and (smart-cut\$4 or smart adj cut\$4 or ("h.sub.2" or hydrogen) near4 (inplant\$4 or implant\$4)))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
27	BRS	21	(((((separat\$4 or cleav\$4) same porous\$4) and (semiconductor or silicion or si) and (smart-cut\$4 or smart adj cut\$4 or ("h.sub.2" or hydrogen) near4 (inplant\$4 or implant\$4))))) not (((separat\$4 or cleav\$4) near4 porous\$4) and (semiconductor or silicion or si) and (smart-cut\$4 or smart adj cut\$4 or ("h.sub.2" or hydrogen) near4 (inplant\$4 or implant\$4)))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
28	BRS	8	(((((separat\$4 or cleav\$4) same porous\$4) and (semiconductor or silicion or si) and (smart-cut\$4 or smart adj cut\$4 or ("h.sub.2" or hydrogen) near4 (inplant\$4 or implant\$4))))) not (((separat\$4 or cleav\$4) near4 porous\$4) and (semiconductor or silicion or si) and (smart-cut\$4 or smart adj cut\$4 or ("h.sub.2" or hydrogen) near4 (inplant\$4 or implant\$4))))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
29	BRS	86	((separat\$4 or cleav\$4) same porous\$4) and (semiconductor or silicion or si) and (smart-cut\$4 or smart adj cut\$4 or ("h.sub.2" or hydrogen) near4 (inplant\$4 or implant\$4))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
30	BRS	30	((separat\$4 or cleav\$4) same porous\$4) and (semiconductor or silicon or si) and (smart-cut\$4 or smart adj cut\$4 or ("h.sub.2" or hydrogen) near4 (inplant\$4 or implant\$4))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
31	IS&R	2	("6602761" or ("6271101")).PN.	USPAT
32	IS&R	11	((("6,020,252" or ("5,985,681" or ("5,882,987" or ("5,374,564" or ("5,714,395" or ("6,331,208" or ("5,371,037" or ("6,171,982" or ("6,342,433" or ("6,294,478" or ("6,271,101")).PN.	USPAT